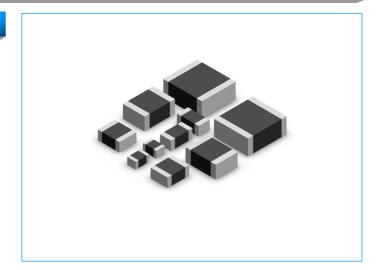




### SV0806H271G0F

#### **Description**

The SV0806H271G0F is based on Multilayer fabrication technology. These components are designed to suppress a variety of transient events, including those specified in IEC 61000-4-2 or other standards used for Electromagnetic Compliance (EMC). The SV0806H271G0F is typically applied to protect integrated circuits and other components at the circuit board level. It can operate over a wider temperature range than zener diodes.



#### **Features**

- Rectangle, sizes serialization for hybrid integrated circuit or printed circuit surface mount components
- There are many side electrode lead-out material, particularly suitable for surface mount technology for solderability and resistance to soldering heat of the stringent requirements
- u Fast response (<1ns)
- u Low leakage current, low clamping voltage
- Suitable for reflow, wave soldering and hot air hand soldering

### **Applications**

- Application for Mother Board, Notebook, Cellular Phone, PDA, handheld device, DSC, DV, Scanner, and Set-Top Box...etc.
- Suitable for Push-Button, Power Line and Low Frequency single line over-voltage protect.





## SV0806H271G0F

### **Electrical Characteristics (25±5℃)**

Symbol	Minimum	Typical	Maximum	Units
V <sub>RMS</sub>	_	_	175	V
V <sub>DC</sub>	_	_	225	V
Vv	243	_	297	V
Vc	_	_	450	V
I <sub>max</sub>	_	_	200	А

 $V_{\text{RMS}}$  - Maximum AC operating voltage the varistor can maintain and not exceed 10 $\mu$ A leakage current.

V<sub>DC</sub> - Maximum DC operating voltage the varistor can maintain and not exceed 10μA leakage current.

 $V_V$  - Voltage across the device measure at 1mA DC current. Equivalent to  $V_{BR}$  "breakdown voltage".

Vc - Maximum peak current across the varistor with 8/20µs waveform and 1A pulse current.

I<sub>max</sub> - Maximum peak current which may be applied with 8/20µs waveform without device failure.





# SV0806H271G0F

## **Shape & Dimensions and Parts & Components**

Shape & Dimensions: See Fig.1 and Table 1. Parts & Components: See Fig.2 and Table 2.

Fig.1

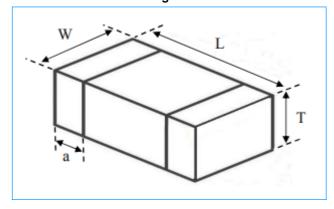


Table 1

Туре	L (mm)	W (mm)	T (mm)	a (mm)
0806	2.3+0.2/-0.2	1.8+0.2/-0.2	2.0 Max.	0.50±0.30

Fig.2

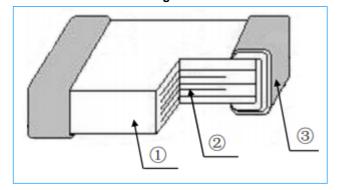


Table 2

Part	1	2	3
Component	ZnO Semiconductor Ceramics for Chip Varistor	Internal Electrode (Ag or Ag-Pd)	Terminal Electrode (Ag/Ni/Sn three layers)

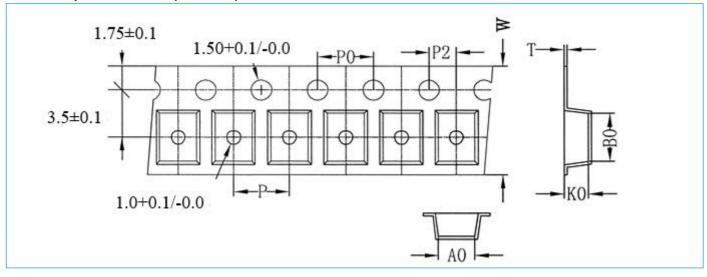




# SV0806H271G0F

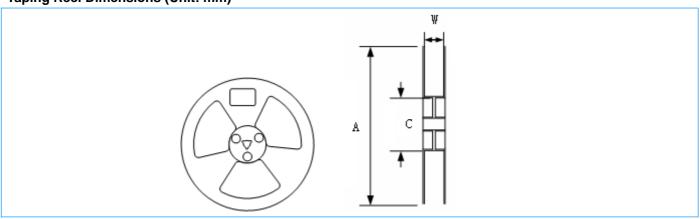
### **Taping**

### **Carrier Tape Dimensions (Unit: mm)**



Туре	A0	B0	K0	T	W	P0	P	P2
	(±0.2)	(±0.2)	Max.	Max.	(±0.3)	(±0.2)	(±0.2)	(±0.2)
0806	2.1	2.5	2.5	0.3	8.0	4.0	4.0	2.0

### Taping Reel Dimensions (Unit: mm)



Torres	Spec.	Dimensions			
Type		A	W	С	
0806	7"	178±2	8.4+2.0/-0.0	58±2	

## **Packaging Quantity**

Туре	Таре	Quantity (pcs/reel)	
0806	Embossed Tape	2000	

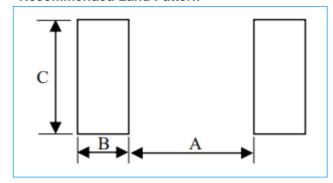




## SV0806H271G0F

## **Soldering Recommendation**

#### **Recommended Land Pattern**

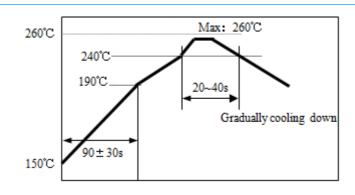


Туре	A (mm)	B (mm)	C (mm)
0806	1.4~1.8	0.8~1.2	1.8~2.2

### **Recommended Soldering Profile**

u Pb Free Solder Paste: Sn/Ag/Cu (96.5/3.0/0.5).

u Max time at max temp: 10sec.u Allowed Reflow time: 2x Max.



### **Notes & Warnings**

- **u** Storage temperature in original packaging: -10~+40 °C.
- u Relative Humidity: ≤70%RH.
- u Keep away from corrosive atmosphere and sunlight.
- u Period of Storage: 12 Months.